

TRANSISTOR (PNP)
Plastic-Encapsulate Transistor
FEATURES

Power dissipation

$$P_{CM}: 2W (T_{amb}=25^{\circ}C)$$

Collector current

$$I_{CM}: -3A$$

Collector-base voltage

$$V_{(BR)CBO}: \text{TIP32: } -40V$$

$$\text{TIP32A: } -60V$$

$$\text{TIP32B: } -80V$$

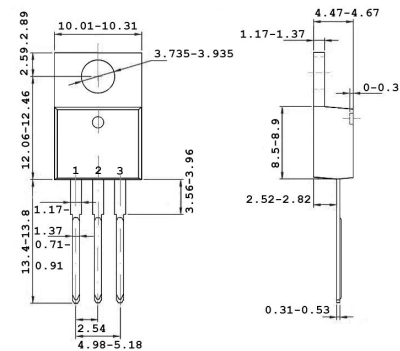
$$\text{TIP32C: } -100V$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55^{\circ}C \text{ to } +150^{\circ}C$$

TO-220

1. BASE
2. COLLECTOR
3. EMITTER



UNIT:mm

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

ELECTRICAL CHARACTERISTICS

Parameters	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	32	$I_C = -100 \mu A, I_E = 0$	-40		V
	32A		-60		
	32B		-80		
	32C		-100		
Collector-emitter breakdown voltage	32	$I_C = -30mA, I_B = 0$	-40		V
	32A		-60		
	32B		-80		
	32C		-100		
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100 \mu A, I_C = 0$	-5		V
Collector cut-off current	32	I_{CBO}	$V_{CB} = -40V, I_E = 0$	-0.2	mA
	32A		$V_{CB} = -60V, I_E = 0$		
	32B		$V_{CB} = -80V, I_E = 0$		
	32C		$V_{CB} = -100V, I_E = 0$		
Collector cut-off current	32/32A	I_{CEO}	$V_{CE} = -30V, I_B = 0$	-0.3	mA
	32B/32C		$V_{CE} = -60V, I_B = 0$	-0.3	
Emitter cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0$		-1	mA
DC current gain	$h_{FE(1)}$	$V_{CE} = -4V, I_C = -3A$	10	50	
	$h_{FE(2)}$	$V_{CE} = -4V, I_C = -1A$	25		
Collector-emitter saturation voltage	V_{CEsat}	$I_C = -3A, I_B = -375mA$		-1.2	V
Base-emitter voltage	$V_{BE(on)}$	$V_{CE} = -4V, I_C = -3A$		-1.8	V
Transition frequency	f_r	$V_{CE} = -10V, I_C = -500mA$	3		MHZ